100V 1.3mΩ TOLL N-Ch Power MOSFET

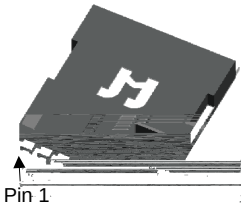
Features

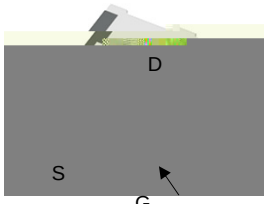
Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th)_Typ}$	2.8	V
I_D (@ V_{GS} = 10V) (1)	411	A
$R_{DS(ON)_Typ}$ (@ V_{GS} = 10V)	1.3	mΩ

Applications

PowerJE®10x12 Bottom





Ordering Information

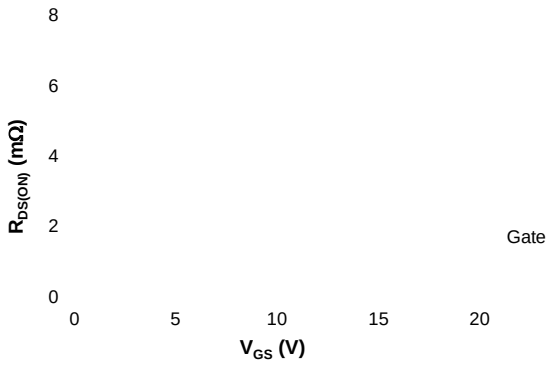
Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1001ATL-13	PowerJE®10x12 (1)	8	SH1001A	1	-55 to 175	13-inch Reel	2000

Note 1: PowerJE® is a registered trademark of JieJie Micro., its package outline is compatible to that of TO-LeadLess (TOLL).

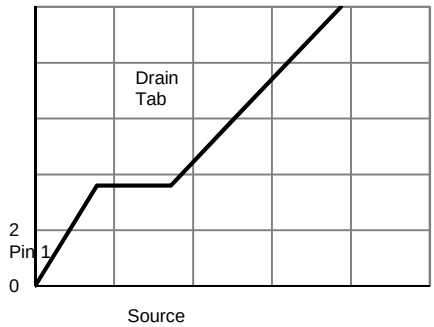
Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
		V_{DS}		V
		V_{GS}		V
Power Dissipation				
Continuous Drain Current (2)	T_C = 25°C	I_D	411	A
	T_C = 100°C		290	
Pulsed Drain Current (3)		I_{DM}	1343	A
Avalanche Current (4)		I_{AS}	50	A
Avalanche Energy (4)		E_{AS}	1250	mJ
(5)	T_C = 25°C	P_D	500	W
	T_C = 100°C		250	
		T_J, T_{STG}		°C

$R_{DS(ON)}$ vs. V_{GS}

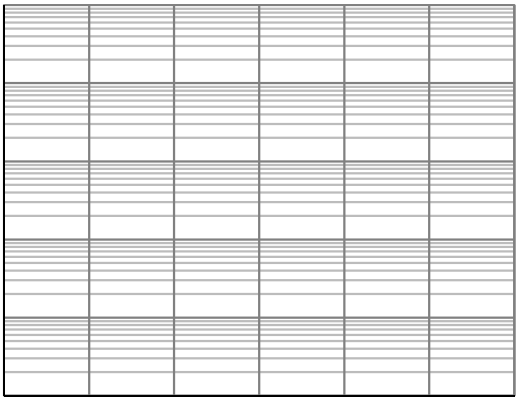


Gate Charge



Jiangsu JieJie Microelectronics Co., Ltd.
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Typical Electrical & Thermal Characteristics



Typical Electrical & Thermal Characteristics

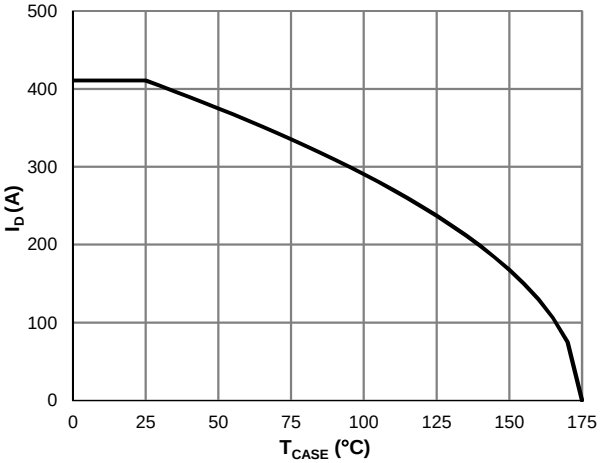


Figure 7: Current De-rating

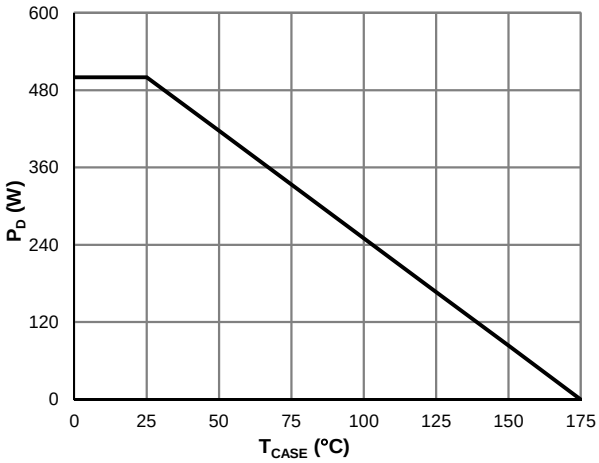
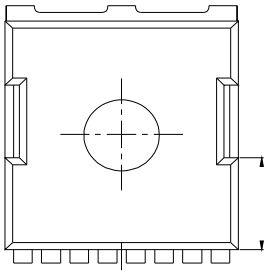


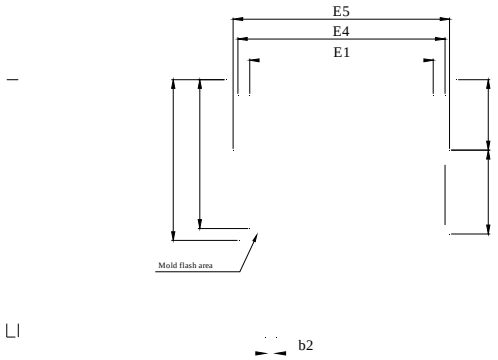
Figure 8: Power De-rating



PowerJE®10x12 Package Information

Packa e Outlines





Side View

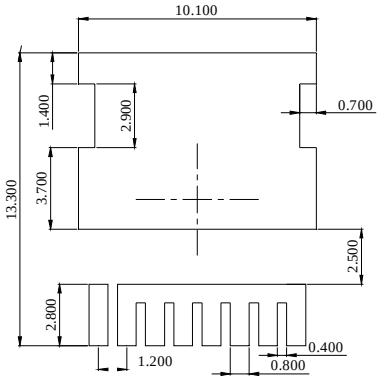
Bottom View

NOTES:
1. Dimeion and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimeiodo include burrs o dfash. Moldflash burrs does N t eceed 0.150mm.

FroN View

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
c	0.40	0.50	0.60
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e		1.20 (BSC)	
	H1	6.55	6.75	6.85
	H2		7.30	
	H3		3.20	
	H4		3.80	
	K1		4.18	
	L	1.70	1.90	2.10
	L1		0.70	
	L2		0.60	
	L4	1.00	1.15	1.30

Recommended SolderiN Footprint



DIMENSIONS:MILLIMETERS